



2DD2656

### LOW V<sub>CE(SAT)</sub> NPN SURFACE MOUNT TRANSISTOR

### **Features**

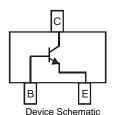
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (2DB1694)
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green Device" (Note 2)

### **Mechanical Data**

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
  Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)







## **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current - Continuous	Ic	1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	2	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	417	°C/W
Power Dissipation (Note 4) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	500	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	250	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	30	_	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 5)	V <sub>(BR)CEO</sub>	30	_	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector Cut-Off Current	I <sub>CBO</sub>	_	_	0.1	μΑ	$V_{CB} = 15V, I_E = 0$
Emitter Cut-Off Current		_	_	0.1	μΑ	$V_{EB} = 6V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)			•			
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	100	350	mV	$I_C = 500 \text{mA}, I_B = 25 \text{mA}$
DC Current Gain		270	_	680	_	$V_{CE} = 2V, I_{C} = 100mA$
SMALL SIGNAL CHARACTERISTICS						_
Output Capacitance	C <sub>obo</sub>	_	5	_	pF	$V_{CB} = 10V$ , $I_E = 0$ , $f = 1MHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	_	270	_	MHz	$V_{CE} = 2V, I_{C} = 100mA,$ f = 100MHz

Notes:

- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- Device mounted on FR-4 PCB with 1 inch<sup>2</sup> copper pad layout.
- Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



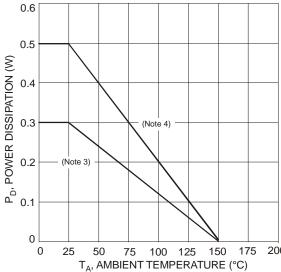


Fig. 1 Power Dissipation vs. Ambient Temperature

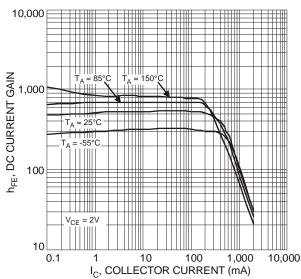
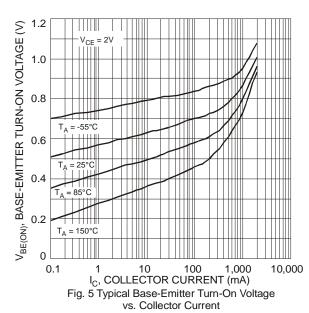
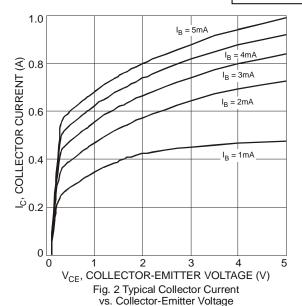


Fig. 3 Typical DC Current Gain vs. Collector Current





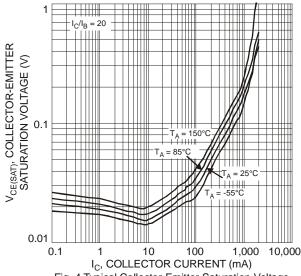


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

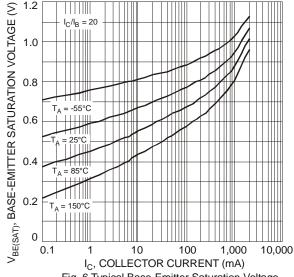
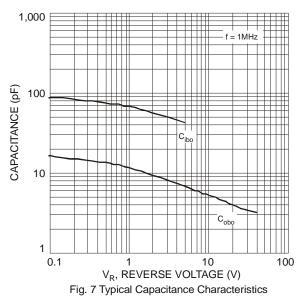


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



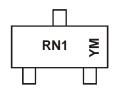


### Ordering Information (Note 6)

Part Number	Case	Packaging
2DD2656-7	SOT-323	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

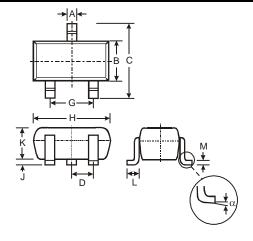


RN1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Date Code Hoy												
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

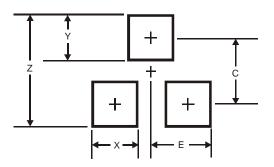
### **Package Outline Dimensions**



SOT-323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	-	-	0.65			
G	1.20	1.40	1.30			
Н	1.80	2.20	2.15			
7	0.0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
M	0.10	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						



### **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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